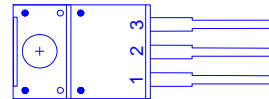
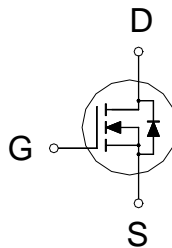




**PRODUCT SUMMARY**

$V_{(BR)DSS}$	$R_{DS(ON)}$	$I_D$
250V	450mΩ	10A



- 1. GATE
- 2. DRAIN
- 3. SOURCE

**ABSOLUTE MAXIMUM RATINGS ( $T_A = 25\text{ °C}$  Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		$V_{DS}$	250	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	$I_D$	10	A
	$T_C = 100\text{ °C}$		6.3	
Pulsed Drain Current <sup>1</sup>		$I_{DM}$	20	
Avalanche Current		$I_{AS}$	6	
Avalanche Energy	$L = 1\text{mH}$	$E_{AS}$	18	mJ
Power Dissipation	$T_C = 25\text{ °C}$	$P_D$	32	W
	$T_C = 100\text{ °C}$		12.8	
Operating Junction & Storage Temperature Range		$T_j, T_{stg}$	-55 to 150	°C

**THERMAL RESISTANCE RATING**

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		3.9	°C / W
Junction-to-Ambient	$R_{\theta JA}$		62.5	

<sup>1</sup>Pulse width limited by maximum junction temperature.

**ELECTRICAL CHARACTERISTICS ( $T_J = 25\text{ °C}$ , Unless Otherwise Noted)**

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
<b>STATIC</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	250			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	2	3	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 250V, V_{GS} = 0V$			1	μA
		$V_{DS} = 200V, V_{GS} = 0V, T_J = 125\text{ °C}$			10	

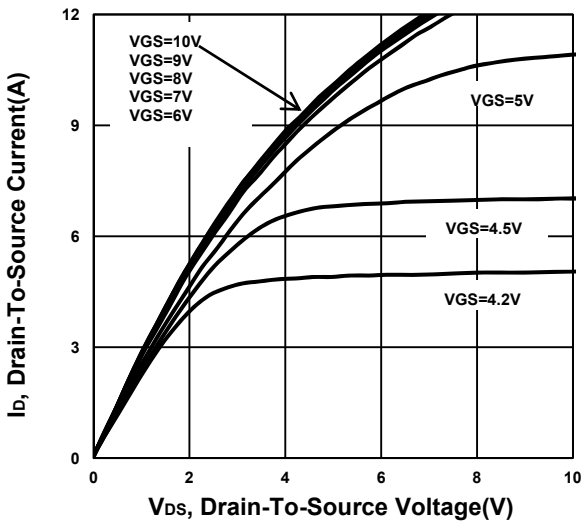
Drain-Source On-State Resistance <sup>1</sup>	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 5A$	340	450	mΩ
		$V_{GS} = 4.5V, I_D = 5A$	452	580	
Forward Transconductance <sup>1</sup>	$g_{fs}$	$V_{DS} = 5V, I_D = 5A$	6.2		S
<b>DYNAMIC</b>					
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	373		pF
Output Capacitance	$C_{oss}$		65		
Reverse Transfer Capacitance	$C_{rss}$		12		
Total Gate Charge <sup>2</sup>	$Q_g$	$V_{DS} = 200V, V_{GS} = 10V,$ $I_D = 10A$	13		nC
Gate-Source Charge <sup>2</sup>	$Q_{gs}$		1.5		
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$		5.6		
Turn-On Delay Time <sup>2</sup>	$t_{d(on)}$	$V_{DD} = 125V,$ $I_D \cong 10A, V_{GS} = 10V, R_{GEN} = 6\Omega$	10		nS
Rise Time <sup>2</sup>	$t_r$		18		
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$		29		
Fall Time <sup>2</sup>	$t_f$		22		
<b>SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (<math>T_J = 25\text{ }^\circ\text{C}</math>)</b>					
Continuous Current <sup>3</sup>	$I_S$			15	A
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = 10A, V_{GS} = 0V$		1	V
Reverse Recovery Time	$t_{rr}$	$I_F = 10A, di_F/dt = 100A / \mu S$	143		nS
Reverse Recovery Charge	$Q_{rr}$		554		nC

<sup>1</sup>Pulse test : Pulse Width  $\leq 300\ \mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

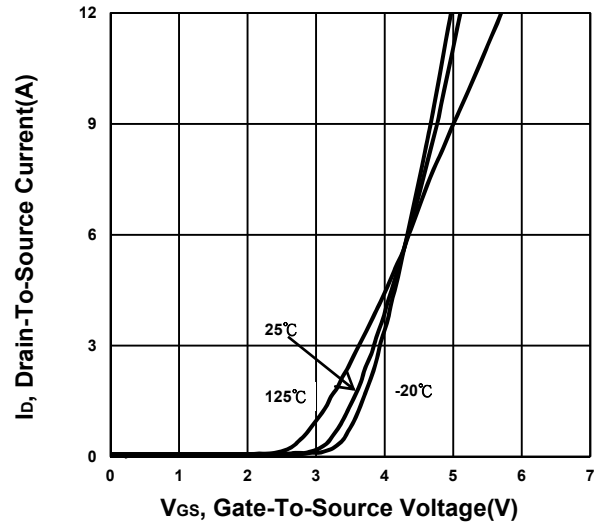
<sup>2</sup>Independent of operating temperature.

<sup>3</sup>Pulse width limited by maximum junction temperature.

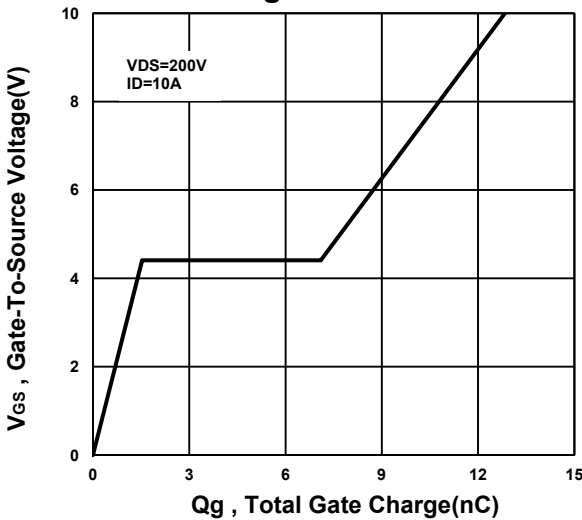
**Output Characteristics**



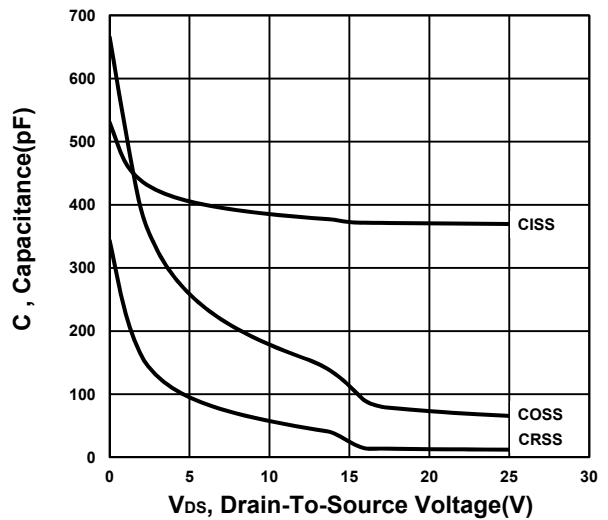
**Transfer Characteristics**



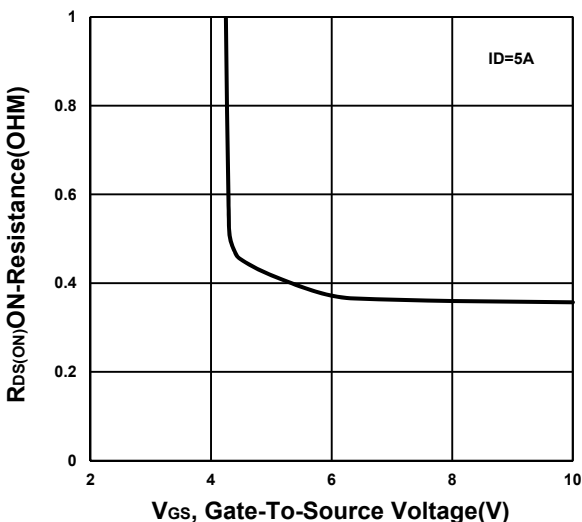
**Gate charge Characteristics**



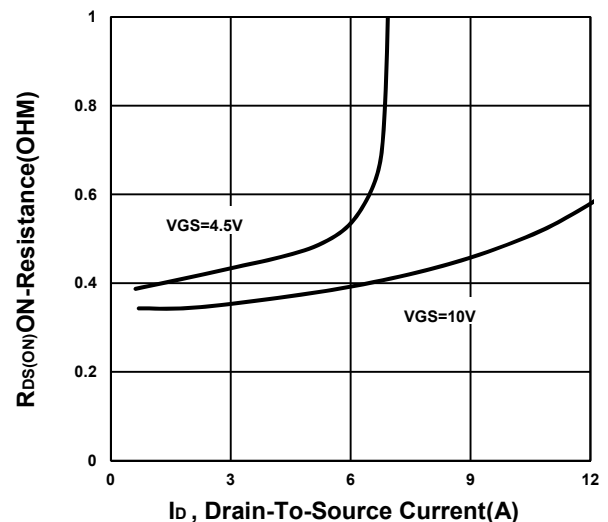
**Capacitance Characteristic**



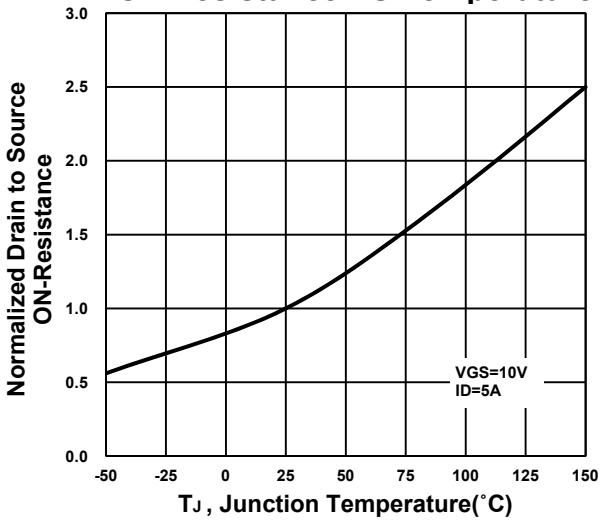
**On-Resistance VS Gate-To-Source**



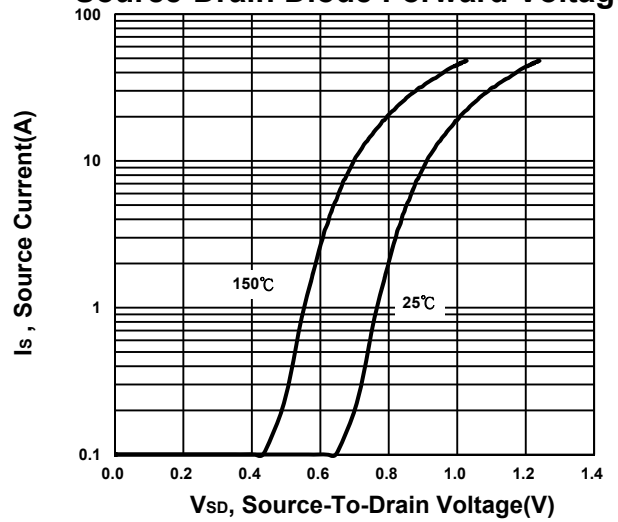
**On-Resistance VS Drain Current**



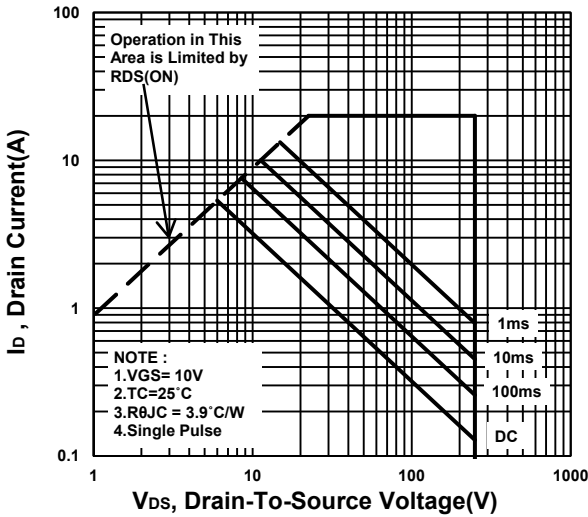
**On-Resistance VS Temperature**



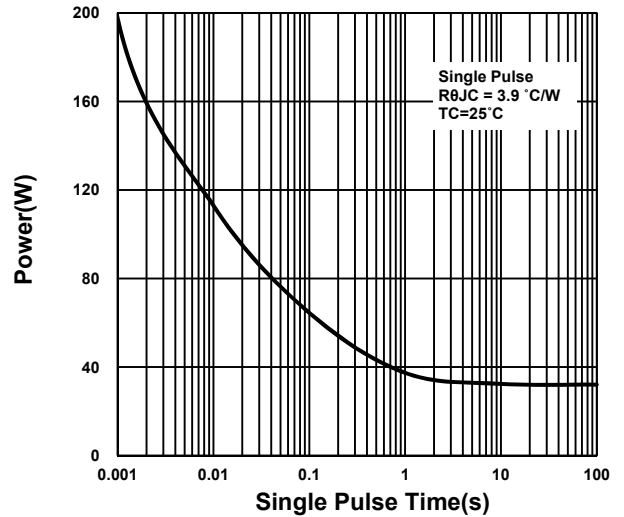
**Source-Drain Diode Forward Voltage**



**Safe Operating Area**



**Single Pulse Maximum Power Dissipation**



**Transient Thermal Response Curve**

